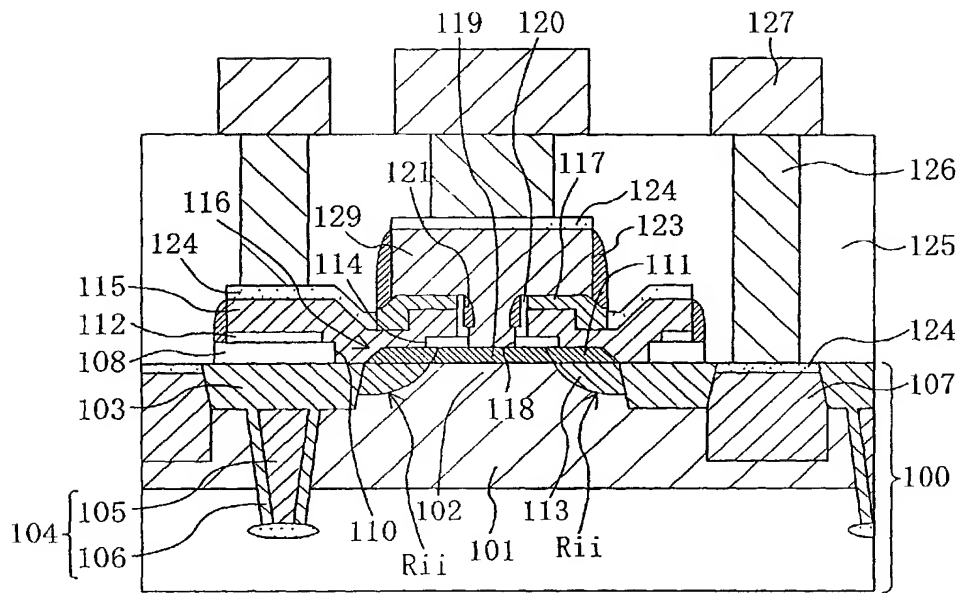


FIG. 1



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FIG. 2(a)

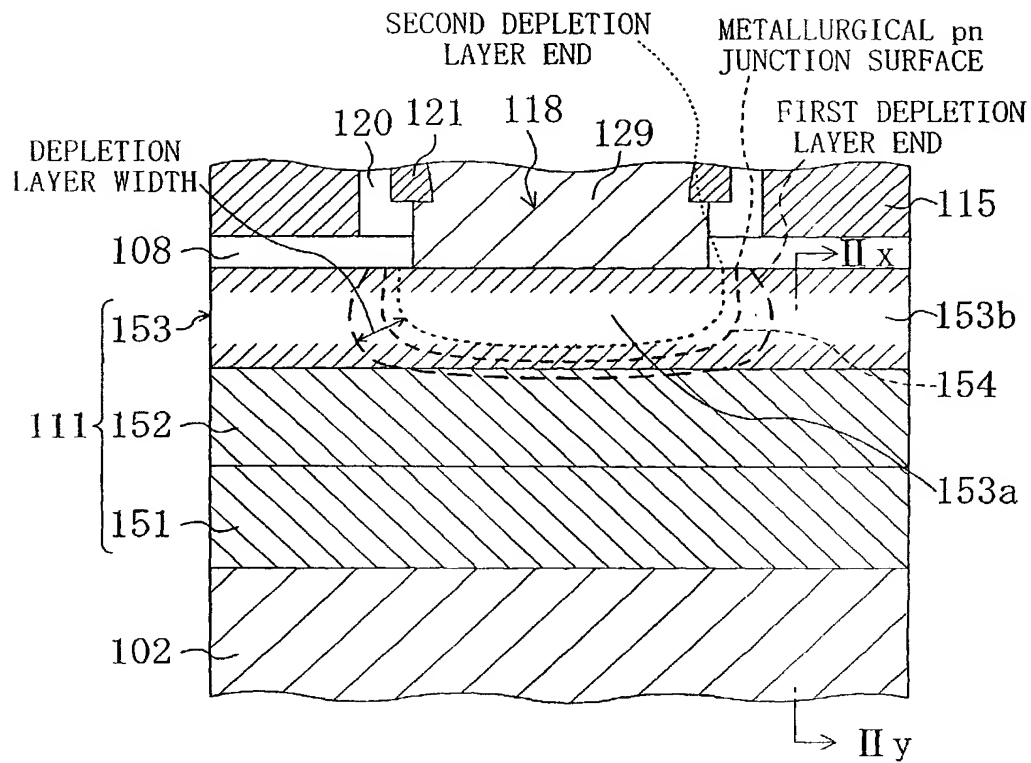


FIG. 2(b)

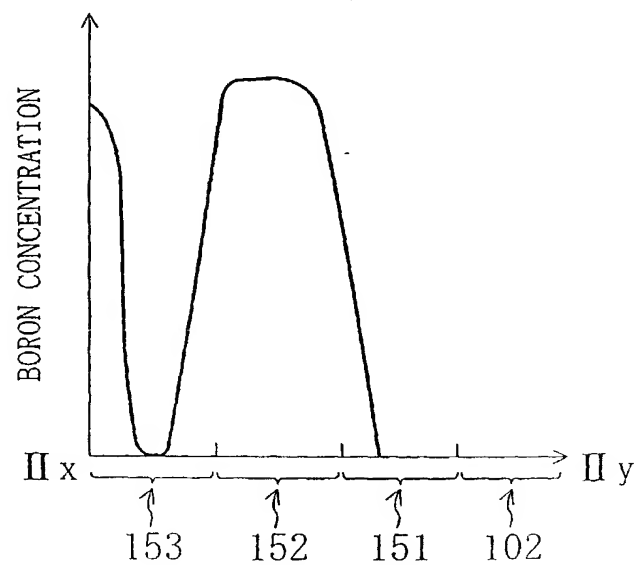


FIG. 3(a)

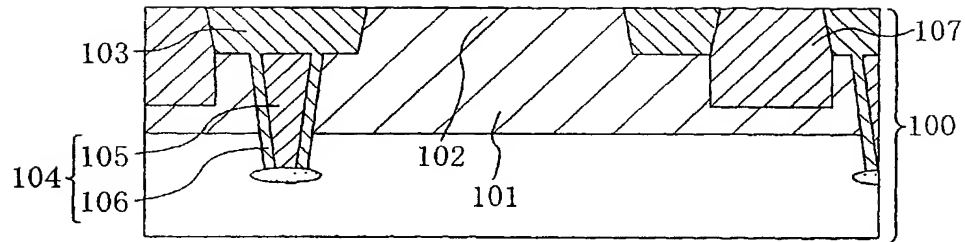
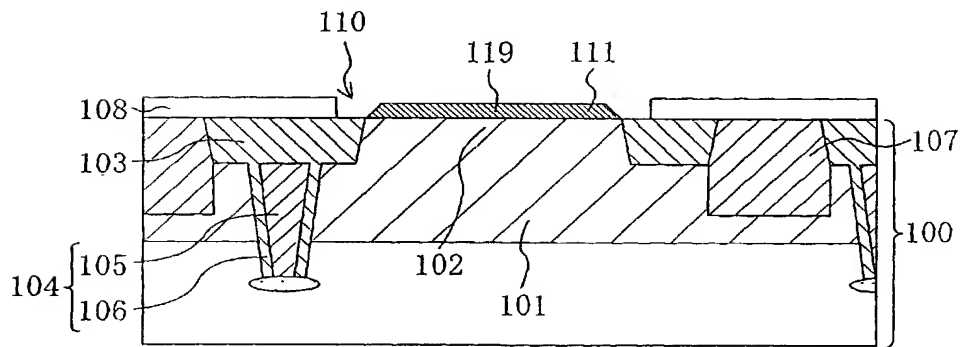


FIG. 3(b)



[illegible]

[illegible][illegible]

FIG. 7(a)

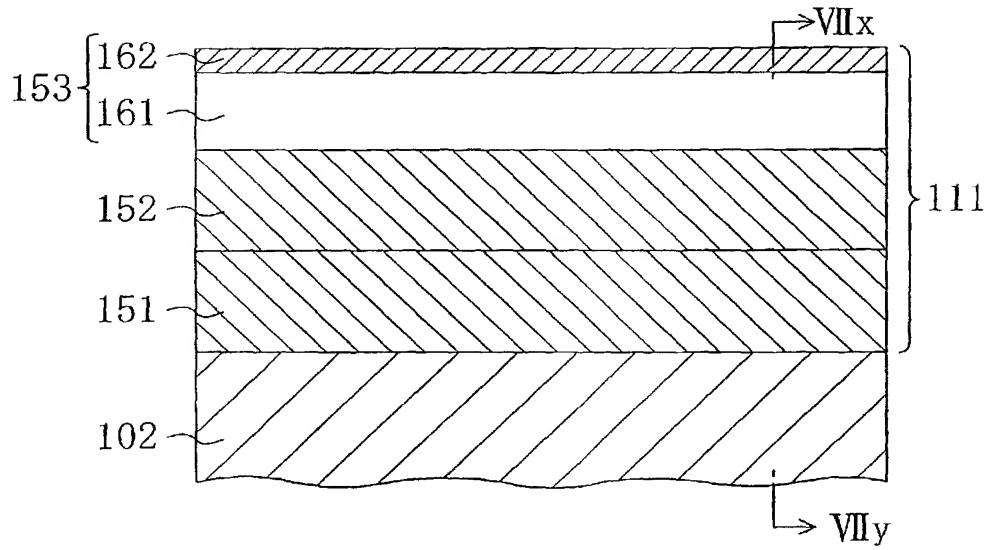


FIG. 7(b)

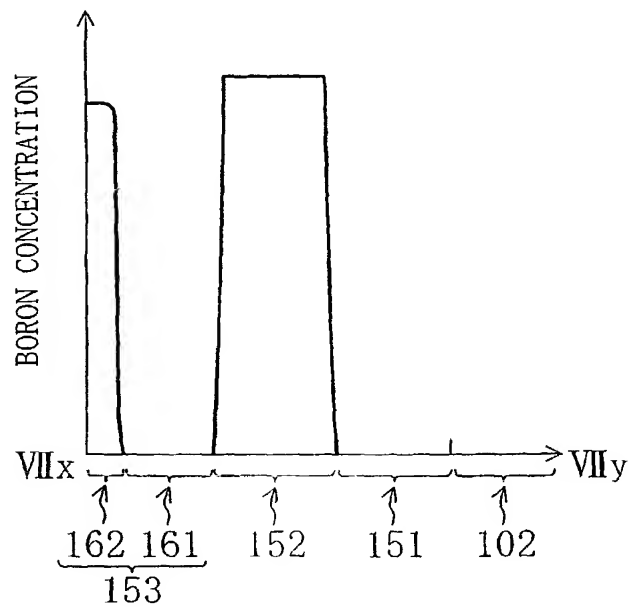


FIG. 8(a)

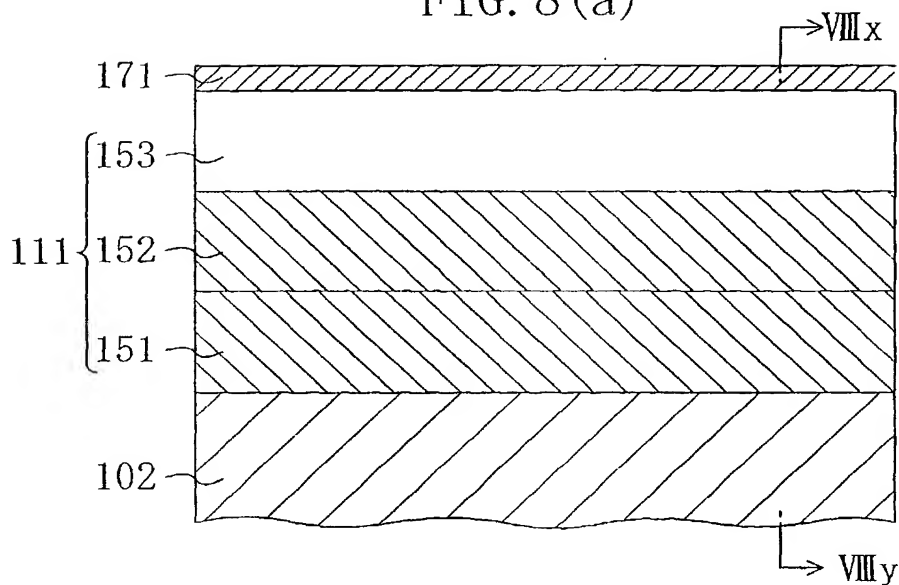


FIG. 8(b)

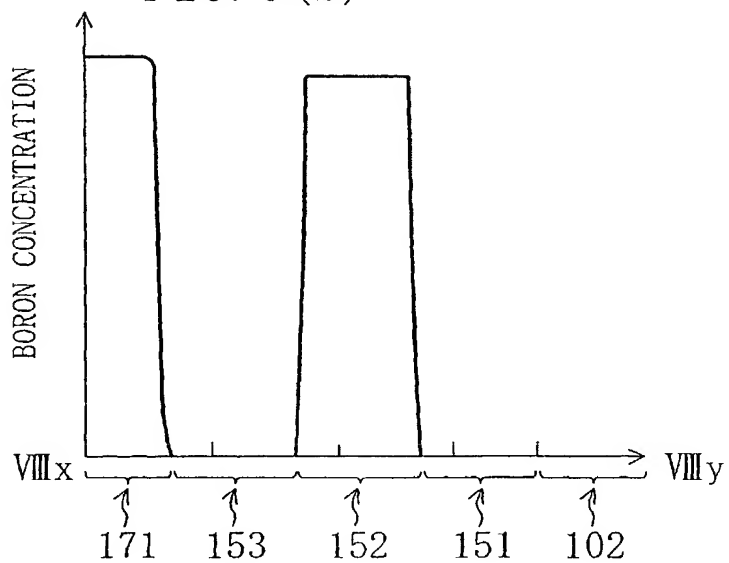


FIG. 9(a)

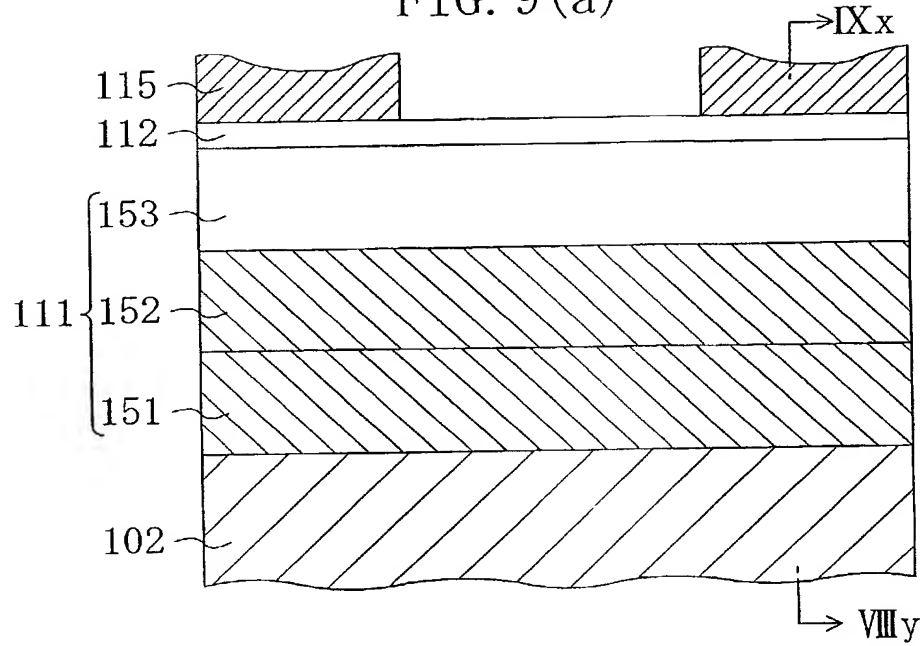


FIG. 9(b)

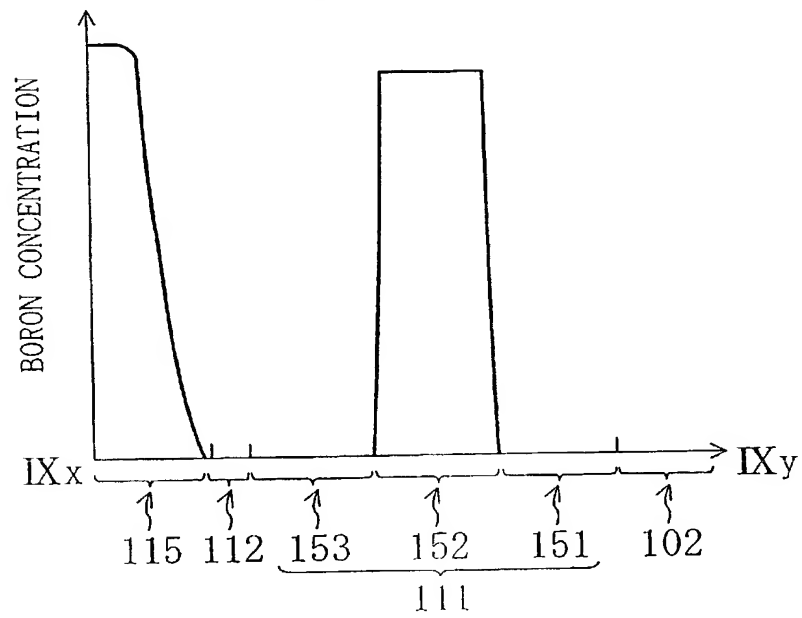
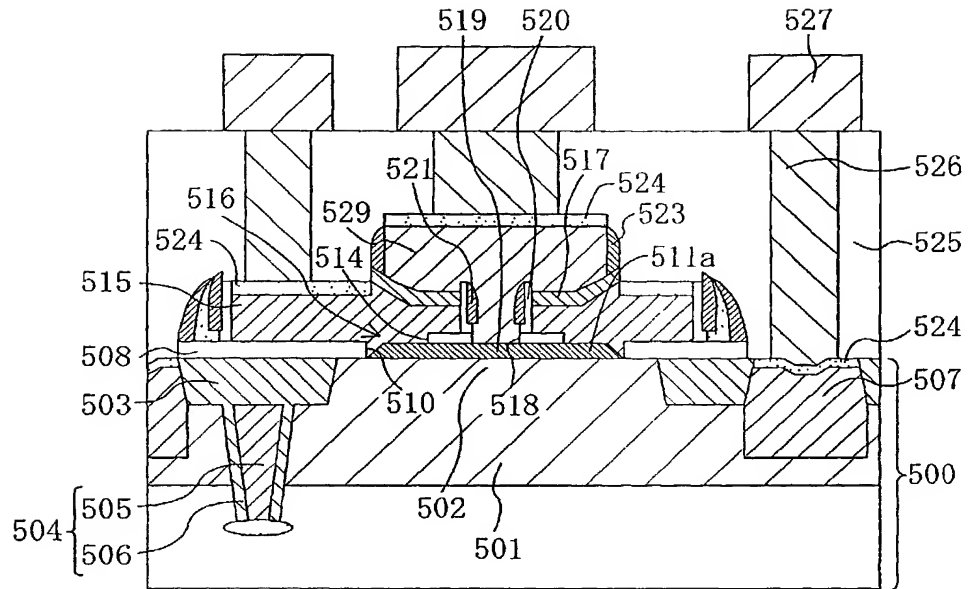


FIG. 10



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FIG. 11(a)

BASE CURRENT, COLLECTOR CURRENT (A)

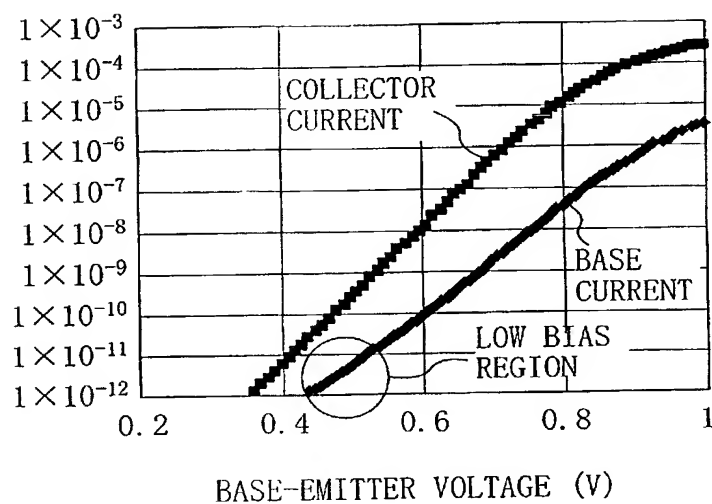


FIG. 11(b)

BASE CURRENT, COLLECTOR CURRENT (A)

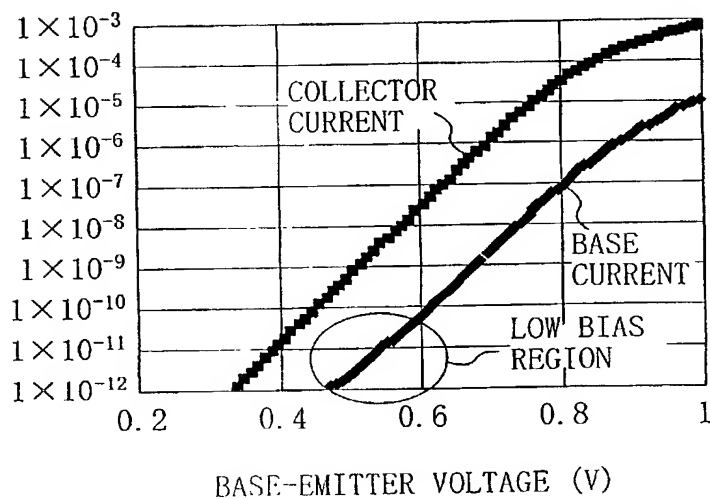


FIG. 12(a)
PRIOR ART

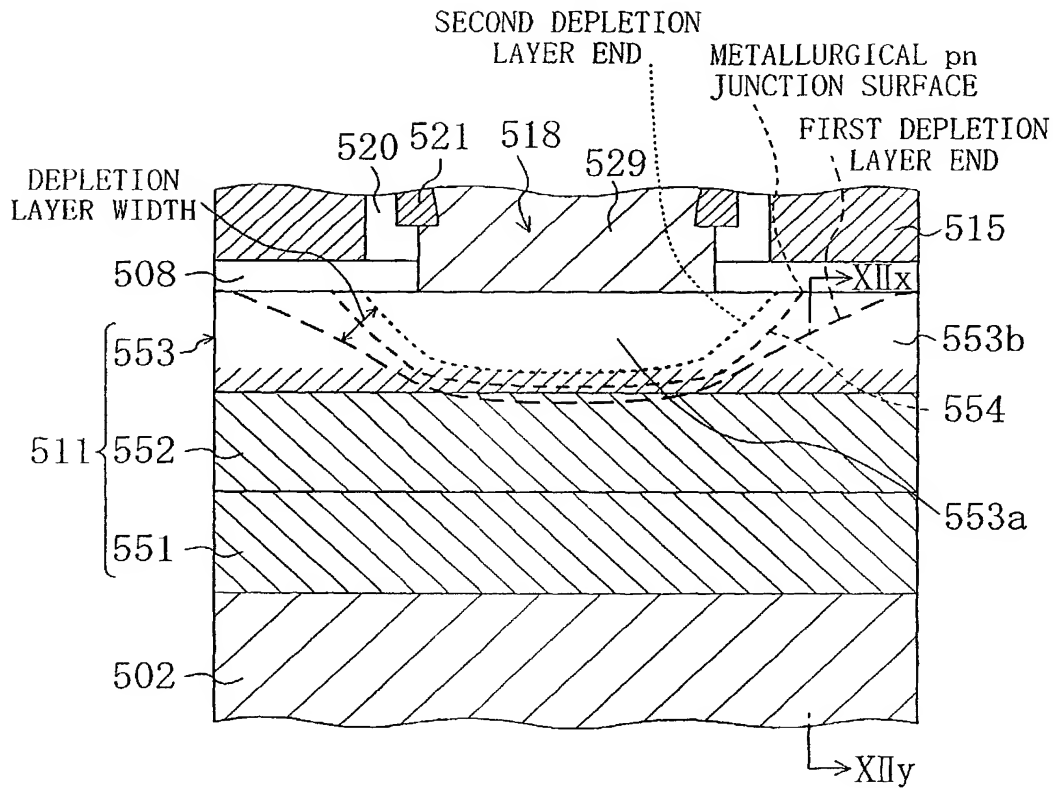
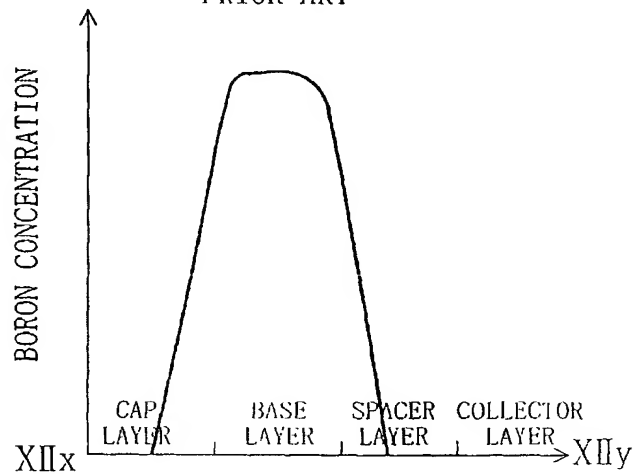


FIG. 12(b)
PRIOR ART



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A detailed cross-sectional diagram of a semiconductor device. The base layer is labeled 100. Above it are several layers and structures: 101, 102, 103, 104 (which includes 105 and 106), 107, 108, 109, 110, 111, 112, 113, 114, 115, 116, 117, 118, 119, 120, 121, 122, 123, 124, 125, 126, 127, 128, 129, 130, 131, 132, 133, 134, 135, 136, 137, 138, 139, 140, 141, 142, 143, 144, 145, 146, 147, 148, 149, 150, 151, 152, 153, 154, 155, 156, 157, 158, 159, 160, 161, 162, 163, 164, 165, 166, 167, 168, 169, 170, 171, 172, 173, 174, 175, 176, 177, 178, 179, 180, 181, 182, 183, 184, 185, 186, 187, 188, 189, 190, 191, 192, 193, 194, 195, 196, 197, 198, 199, 200. The diagram shows various doped regions, insulating layers, and structural elements typical of a microelectronic device.